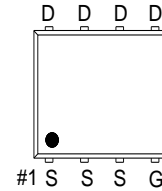
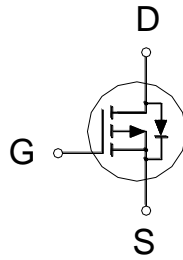


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	20m Ω	-22A



G : GATE
D : DRAIN
S : SOURCE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current ⁴	$T_C = 25\text{ }^\circ\text{C}$	I_D	-22	A
	$T_C = 100\text{ }^\circ\text{C}$		-14	
	$T_A = 25\text{ }^\circ\text{C}$		-9	
	$T_A = 70\text{ }^\circ\text{C}$		-7	
Pulsed Drain Current ¹		I_{DM}	-40	
Avalanche Current		I_{AS}	-23	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	26	mJ
Power Dissipation ³	$T_C = 25\text{ }^\circ\text{C}$	P_D	17	W
	$T_C = 100\text{ }^\circ\text{C}$		7	
	$T_A = 25\text{ }^\circ\text{C}$		3	
	$T_A = 70\text{ }^\circ\text{C}$		2	
Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10\text{s}$			40	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		65	
Junction-to-Case	Steady-State	$R_{\theta JC}$		7.2	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ }^\circ\text{C}$.

³The Power dissipation is based on $R_{\theta JA} t \leq 10\text{s}$ value.

⁴Package limitation current is -21A

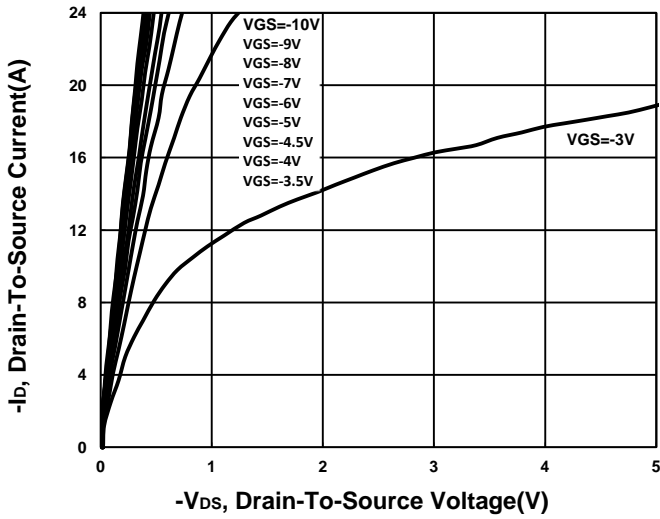
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.3	-1.6	-2.3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -24V, V _{GS} = 0V			-1	μA
		V _{DS} = -20V, V _{GS} = 0V, T _J = 55 °C			-10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = -10V, I _D = -7A		15	20	mΩ
		V _{GS} = -4.5V, I _D = -7A		23	30	
Forward Transconductance ¹	g _{fs}	V _{DS} = -10V, I _D = -7A		25		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz		1009		pF
Output Capacitance	C _{oss}			154		
Reverse Transfer Capacitance	C _{rss}			121		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		8		Ω
Total Gate Charge ²	Q _{g(VGS=-10V)}	V _{DS} = -15V, I _D = -7A		21		nC
	Q _{g(VGS=-4.5V)}			11		
Gate-Source Charge ²	Q _{gs}			3		
Gate-Drain Charge ²	Q _{gd}			6		
Turn-On Delay Time ²	t _{d(on)}		V _{DD} = -15V I _D ≅ -7A, V _{GS} = -10V, R _{GEN} = 6Ω		22	
Rise Time ²	t _r			16		
Turn-Off Delay Time ²	t _{d(off)}			50		
Fall Time ²	t _f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				-13	A
Forward Voltage ¹	V _{SD}	I _F = -7A, V _{GS} = 0V			-1.3	V
Reverse Recovery Time	t _{rr}	I _F = -7A, di _F /dt = 100 A / μS		11		nS
Reverse Recovery Charge	Q _{rr}			3		nC

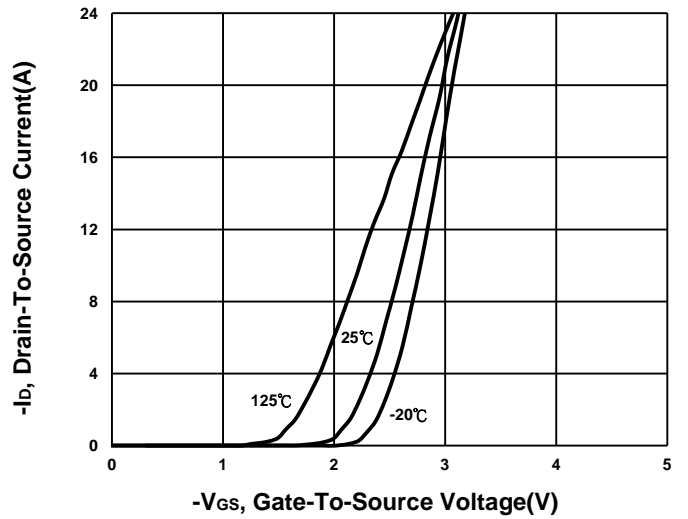
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

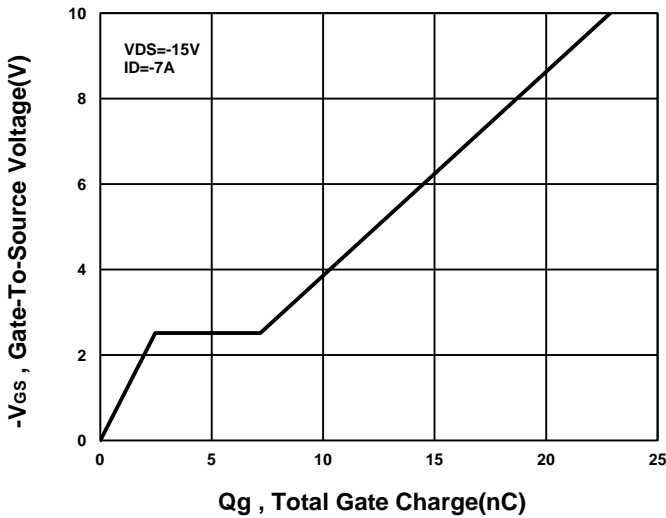
Output Characteristics



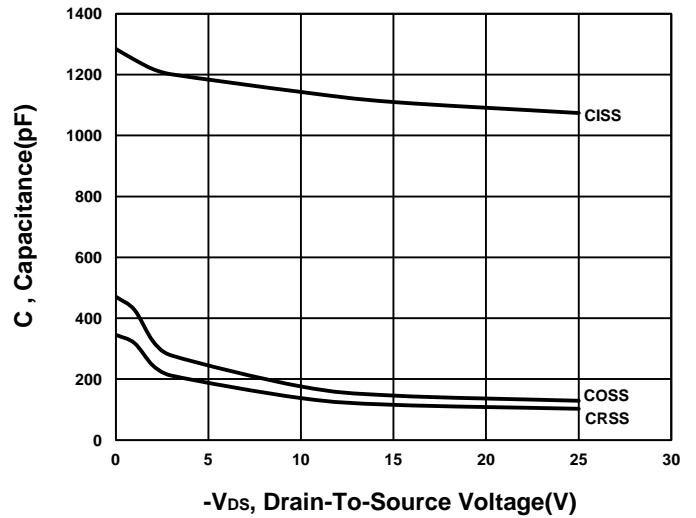
Transfer Characteristics



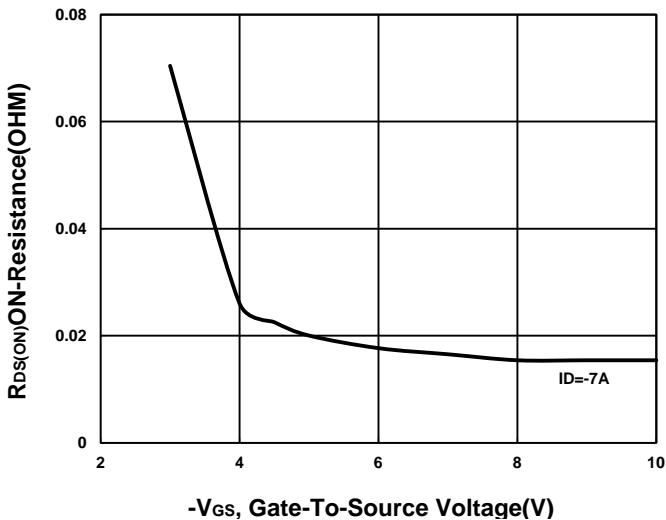
Gate charge Characteristics



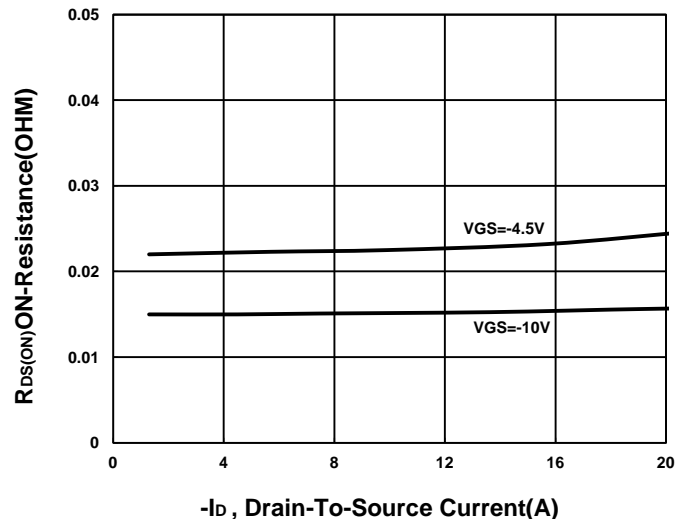
Capacitance Characteristic



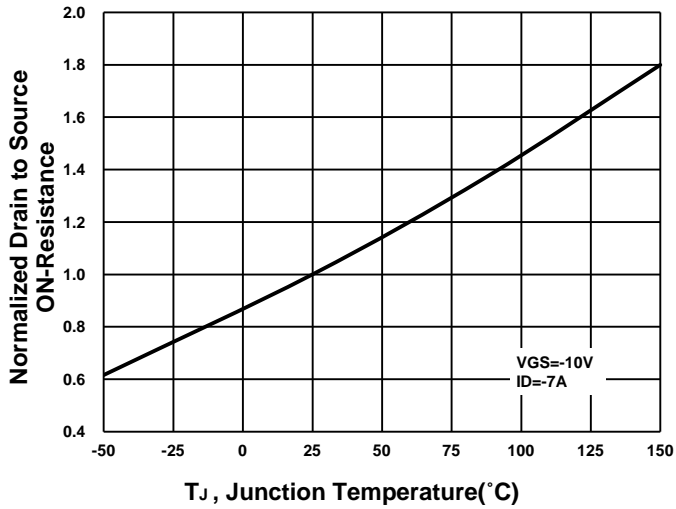
On-Resistance VS Gate-To-Source



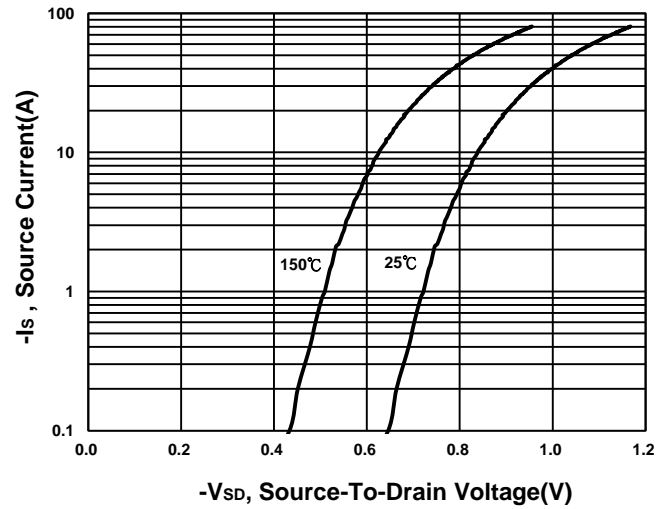
On-Resistance VS Drain Current



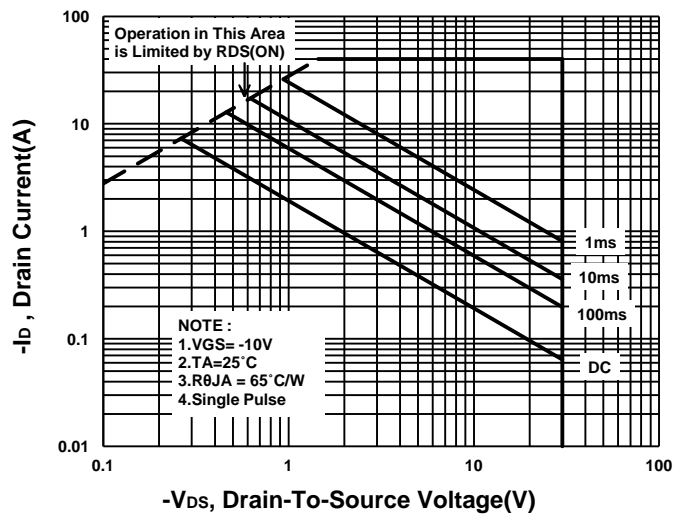
On-Resistance VS Temperature



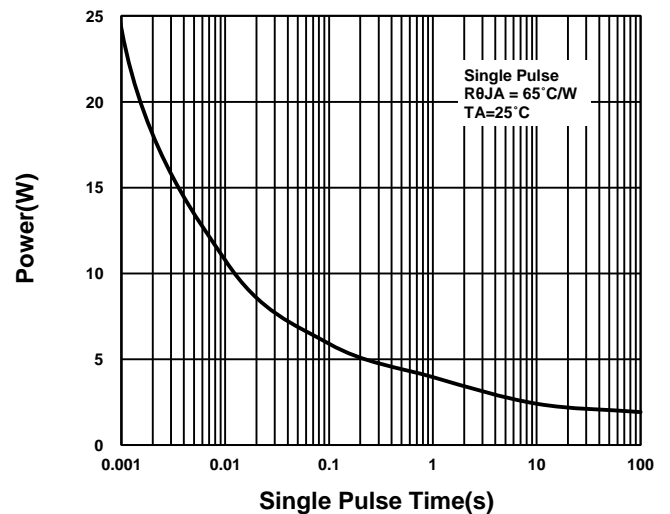
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

